

REMARKS

In the above-identified Office Action all of the pending claims were rejected as being anticipated by the cited Isogai patent. As understood by Applicants, the rejection is based on an interpretation of Isogai as disclosing a first conductivity type first semiconductor region 101 disposed in a pixel region 1, and a second conductivity type second semiconductor region 18 provided in the first semiconductor region, for accumulating photoelectric carriers in a floating state; a wiring 24 connecting the second semiconductor region 18 to a circuit element 4 at a position outside of the pixel region; and, a conductor 23 disposed through an insulator 33 on the wiring 24 positioned in the pixel region 1, thereby supplying a stable voltage and being formed by the same layer as a photo-screen of the pixel region.

Applicants' understanding, however, is that the region 18 of Isogai, characterized in the Office Action as the second semiconductor region, is a region for ejecting photo carriers excessively generated by the photodiode 1, and for controlling a voltage of P-gate region 15 of JFET 2 thereby amplifying the photo carriers. Also, the region 18 is optically shielded by a reset drain wiring 24. Therefore, the region 18 can not receive light, as is apparent from Fig. 4 of Isogai.

In Applicants' invention, on the other hand, as set forth in Claim 1, the first and second semiconductor regions may be deemed to correspond respectively to regions 12 and 101 of Isogai, but the photo carriers generated in the regions 12 and 101 of Isogai are transferred by a transfer gate 3 to JFET 2 for being amplified. Accordingly, the device of

Isogai is not a sensor wherein the wiring is connected electrically to the second semiconductor region as required in Applicants claims.

Moreover, Isogai does not disclose or suggest wiring connected to the region 12, nor a conductor disposed through an insulator on the wiring, for maintaining a predetermined voltage as in Applicants' claimed invention.

Furthermore, Isogai does not disclose or suggest the solving of a special technical problem as in the present invention, wherein an adverse effect due to an external low frequency noise, such as a radiation noise, would be caused in the region which is apertured for accumulating the photo carriers in the floating state, and which has a wiring to provide a reading signal.

For these various reasons it is believed that all of the pending claims are allowable. Accordingly, the issuance of a Formal Notice of Allowance is solicited.

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our below listed address.

Respectfully submitted,


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